

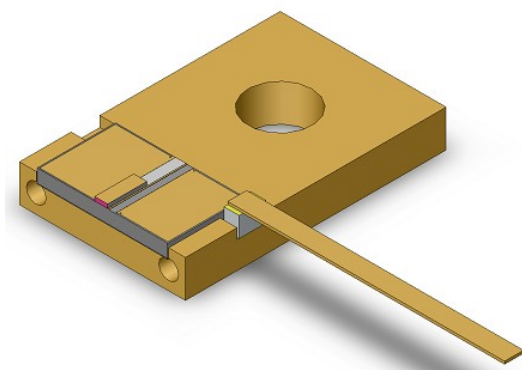
## BAL 1113: 1450nm / 0.5W Broad Area Laser Diode Chip

7.1.2.SP.1113 Rev B
Preliminary Model

### Description

COVEGA's broad area laser diode is based on a highly efficient InP/InGaAsP Quantum Well (QW) layer structure.

Advanced MBE epitaxial wafer growth techniques and die bonding processes enable reliable high-power laser diode operation.



### Features

#### Applications

- ✓ Medical
- ✓ Industrial
- ✓ Source Laser for Free Space Optical Wireless Communication

- High Optical Output Power
- High Slope Efficiency
- Numerous Packaging Options

### Specifications

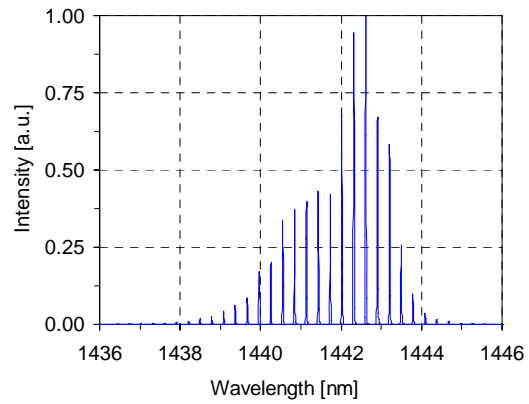
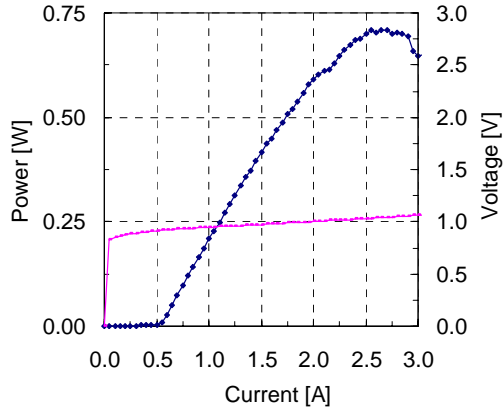
CW, T (Chip) = 25°C

Parameter		Min	Typ	Max	
Operating Current	$I_{OP}$		1.7	2.2	A
Center Wavelength	$\lambda_C$	1425	1450	1475	nm
Spectral Bandwidth (rms)	$\Delta\lambda$		7	15	nm
Output Power over C-Band	$P_{OUT}$	0.5			W
Threshold Current	$I_{TH}$		0.4	0.7	A
Slope Efficiency	$\Delta P/\Delta I$	0.3	0.5		W/A
Forward Voltage	V		3.0	4.0	V
Chip Length	L		0.6		mm
Emitter Width	W		100		$\mu\text{m}$
Beam Divergence Angle (FWHM)					
- Transverse	$\theta_T$		28	36	deg
- Lateral	$\theta_L$		8	14	deg

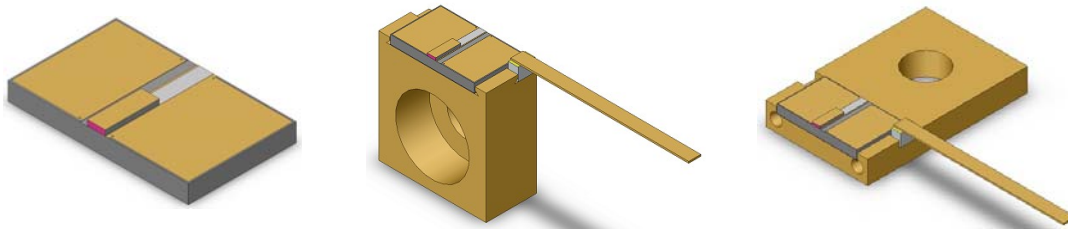
SPECIFICATIONS SUBJECT TO CHANGE WITHOUT NOTICE

## BAL 1113

### Performance



### Packaging



Chip on Submount

C-Mount

CT-Mount

### Ordering Information

BAL 1113 - XXX	
XXX	
<b>Submount</b>	
COS = Chip on submount	
CMN = C-Mount	
CTM = CT-Mount	
ZZZ = Custom Mount	

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